## 1.55 µm Laser Diode with EA Modulator

# HITACHI

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### **Description**

The HL1569AF is a 1.55  $\mu$ m InGaAsP distributed-feedback laser diode (DFB-LD) with a multi-quantum well (MQW) structure. An electroabsorption (EA) modulator is integrated with the laser diode. It is suitable as a light source for high-bit-rate, long haul fiberoptic communication systems, such as 2.5 Gbps external modulation systems for up to 600 km.

#### **Features**

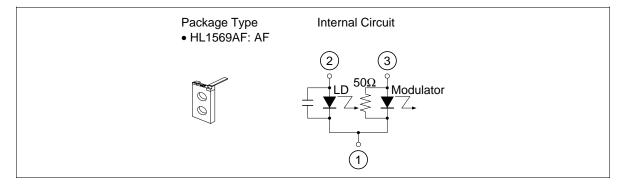
• Long wavelength output:  $\lambda p = 1550 \text{ nm Typ}$ 

• High extinction ratio: 15 dB Min at  $V_{R(EA)} = -2 \text{ V}$ 

• Fast pulse response:  $t_r/t_f \le 80 \text{ ps}$ 

• Dynamic single longitudinal mode: Sr = 40 dB Typ

• Package: open air package (chip on carrier) with micro strip-line





## **Absolute Maximum Ratings** $(T_C = 25^{\circ}C)$

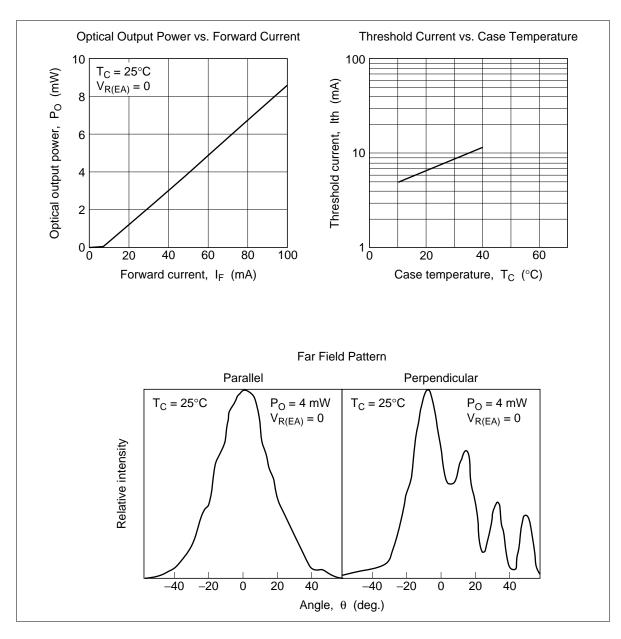
Item	Symbol	Value	Unit	
LD forward current	I <sub>F</sub>	100	mA	
Laser diode reverse voltage	$V_{R(LD)}$	2	V	
Modulator reverse voltage	$V_{R(EA)}$	5	V	
Operating temperature	Topr	+10 to +40	°C	
Storage temperature *	Tstg	-40 to +85	°C	

Note: without condensation

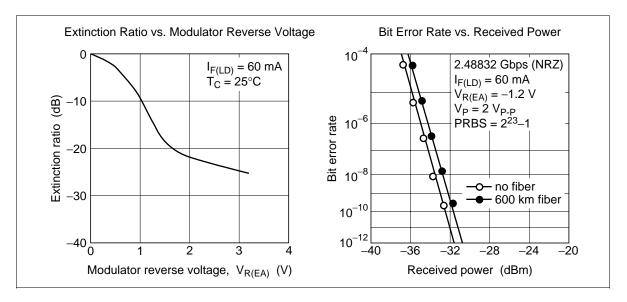
# Optical and Electrical Characteristics ( $T_C = 25^{\circ}C$ )

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Threshold current	lth	_	10	20	mA	
Optical output power	Po	4	_	_	mW	$I_{F(LD)} = 60 \text{ mA}, V_{R(EA)} = 0 \text{ V}$
Extinction ratio	ER	15	_	_	dB	$I_{F(LD)} = 60 \text{ mA}, V_{R(EA)} = 0/-2 \text{ V}$
Lasing wavelength	λр	1530	1550	1570	nm	2.5 Gbps (NRZ)
Side-mode suppression ratio	Sr	30	40	_	dB	2.5 Gbps (NRZ)
Beam divergence parallel to the junction	θ//	_	30	_	deg.	P <sub>o</sub> = 4 mW, FWHM
Beam divergence parpendicular to the junction	θΤ	_	40	_	deg.	P <sub>o</sub> = 4 mW, FWHM
Rise time	t <sub>r</sub>	_	_	80	ps	2.5 Gbps (NRZ)
Fall time	t <sub>f</sub>	_	_	80	ps	2.5 Gbps (NRZ)
Cutoff frequency	S <sub>21</sub>	4	_	_	GHz	$I_{F(LD)} = 60 \text{ mA}, V_{R(EA)} = -1 \text{ V}$
RF return loss	S <sub>11</sub>	10	_	_	dB	$I_{F(LD)} = 60 \text{ mA}, V_{R(EA)} = -1 \text{ V},$ f \le 3 GHz

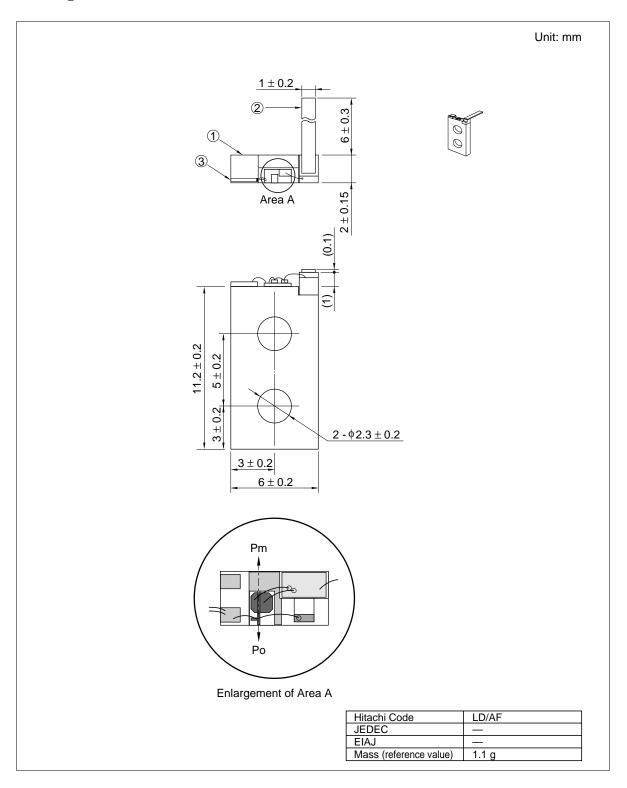
### **Typical Characteristic Curves**



#### **Typical Characteristic Curves (cont)**



## **Package Dimensions**



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#### **Cautions**

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